MARKING DIAGRAMS



# Inverting Regulator - Buck, Boost, Switching

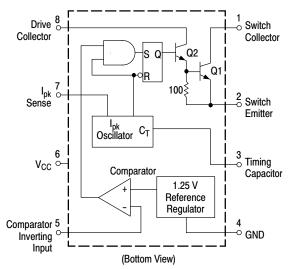
# 1.5 A

# MC34063A, MC33063A, SC33063A, NCV33063A

The MC34063A Series is a monolithic control circuit containing the primary functions required for DC-to-DC converters. These devices consist of an internal temperature compensated reference, comparator, controlled duty cycle oscillator with an active current limit circuit, driver and high current output switch. This series was specifically designed to be incorporated in Step-Down and Step-Up and Voltage-Inverting applications with a minimum number of external components. Refer to Application Notes AN920A/D and AN954/D for additional design information.

#### **Features**

- Operation from 3.0 V to 40 V Input
- Low Standby Current
- Current Limiting
- Output Switch Current to 1.5 A
- Output Voltage Adjustable
- Frequency Operation to 100 kHz
- Precision 2% Reference
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

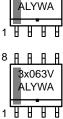


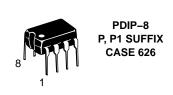
This device contains 79 active transistors.

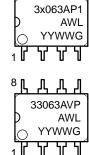
Figure 1. Representative Schematic Diagram

# 8 <u>R R R</u> 3x063 ALYWA









c = 3 or 4

A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or • = Pb-Free Package

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

Figure 2. Pin Connections

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Power Supply Voltage	V <sub>CC</sub>	40	Vdc
Comparator Input Voltage Range	$V_{IR}$	-0.3 to +40	Vdc
Switch Collector Voltage	V <sub>C(switch)</sub>	40	Vdc
Switch Emitter Voltage (V <sub>Pin 1</sub> = 40 V)	V <sub>E(switch)</sub>	40	Vdc
Switch Collector to Emitter Voltage	V <sub>CE(switch)</sub>	40	Vdc
Driver Collector Voltage	V <sub>C(driver)</sub>	40	Vdc
Driver Collector Current (Note 1)	I <sub>C(driver)</sub>	100	mA
Switch Current	I <sub>SW</sub>	1.5	Α
Power Dissipation and Thermal Characteristics			
Plastic Package, P, P1 Suffix			
T <sub>A</sub> = 25°C	P <sub>D</sub>	1.25	W
Thermal Resistance	$R_{ hetaJA}$	115	°C/W
SOIC Package, D Suffix			
$T_A = 25^{\circ}C$	$P_{D}$	625	mW
Thermal Resistance	$R_{ heta JA}$	160	°C/W
Thermal Resistance	$R_{ heta JC}$	45	°C/W
DFN Package			
$T_A = 25^{\circ}C$	P <sub>D</sub>	1.25	mW
Thermal Resistance	$R_{ hetaJA}$	80	°C/W
Operating Junction Temperature	TJ	+150	°C
Operating Ambient Temperature Range	T <sub>A</sub>		°C
MC34063A		0 to +70	
MC33063AV, NCV33063A		-40 to +125	
MC33063A, SC33063A		-40 to +85	
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

<sup>1.</sup> Maximum package power dissipation limits must be observed.

This device series contains ESD protection and exceeds the following tests: Human Body Model 4000 V per MIL-STD-883, Method 3015.
 Machine Model Method 400 V.

<sup>3.</sup> NCV prefix is for automotive and other applications requiring site and change control.

**ELECTRICAL CHARACTERISTICS** ( $V_{CC} = 5.0 \text{ V}$ ,  $T_A = T_{low}$  to  $T_{high}$  [Note 4], unless otherwise specified.)

Characteristics	Symbol	Min	Тур	Max	Unit
OSCILLATOR					
Frequency (V <sub>Pin 5</sub> = 0 V, C <sub>T</sub> = 1.0 nF, T <sub>A</sub> = 25°C)	f <sub>osc</sub>	24	33	42	kHz
Charge Current (V <sub>CC</sub> = 5.0 V to 40 V, T <sub>A</sub> = 25°C)	I <sub>chg</sub>	24	35	42	μΑ
Discharge Current (V <sub>CC</sub> = 5.0 V to 40 V, T <sub>A</sub> = 25°C)	I <sub>dischg</sub>	140	220	260	μΑ
Discharge to Charge Current Ratio (Pin 7 to V <sub>CC</sub> , T <sub>A</sub> = 25°C)	I <sub>dischg</sub> /I <sub>chg</sub>	5.2	6.5	7.5	-
Current Limit Sense Voltage (I <sub>chg</sub> = I <sub>dischg</sub> , T <sub>A</sub> = 25°C)	V <sub>ipk(sense)</sub>	250	300	350	mV
OUTPUT SWITCH (Note 5)					
Saturation Voltage, Darlington Connection (I <sub>SW</sub> = 1.0 A, Pins 1, 8 connected)	V <sub>CE(sat)</sub>	-	1.0	1.3	V
Saturation Voltage (Note 6) (I <sub>SW</sub> = 1.0 A, R <sub>Pin 8</sub> = 82 $\Omega$ to V <sub>CC</sub> , Forced $\beta \simeq 20$ )	V <sub>CE(sat)</sub>	-	0.45	0.7	V
DC Current Gain (I <sub>SW</sub> = 1.0 A, V <sub>CE</sub> = 5.0 V, T <sub>A</sub> = 25°C)	h <sub>FE</sub>	50	75	-	-
Collector Off–State Current (V <sub>CE</sub> = 40 V)	I <sub>C(off)</sub>	_	0.01	100	μΑ
COMPARATOR					
Threshold Voltage $T_A = 25^{\circ}C$ $T_A = T_{low} \text{ to } T_{high}$	V <sub>th</sub>	1.225 1.21	1.25 –	1.275 1.29	V
Threshold Voltage Line Regulation (V <sub>CC</sub> = 3.0 V to 40 V) MC33063, MC34063 MC33063V, NCV33063	Reg <sub>line</sub>	- -	1.4 1.4	5.0 6.0	mV
Input Bias Current (V <sub>in</sub> = 0 V)	I <sub>IB</sub>	-	-20	-400	nA
TOTAL DEVICE					
Supply Current ( $V_{CC}$ = 5.0 V to 40 V, $C_T$ = 1.0 nF, Pin 7 = $V_{CC}$ , $V_{Pin 5}$ > $V_{th}$ , Pin 2 = GND, remaining pins open)	Icc	_	_	4.0	mA
		-	-	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. T<sub>low</sub> = 0°C for MC34063, SC34063; −40°C for MC33063, SC33063, MC33063V, NCV33063

T<sub>high</sub> = +70°C for MC34063, SC34063; +85°C for MC33063, SC33063; +125°C for MC33063V, NCV33063

5. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.

6. If the output switch is driven into hard saturation (non–Darlington configuration) at low switch currents (≤ 300 mA) and high driver currents

Forced  $\beta$  of output switch :  $\frac{IC \text{ output}}{IC \text{ driver} - 7.0 \text{ mA}^*} \ge 10$ 

<sup>(≥ 30</sup> mA), it may take up to 2.0 µs for it to come out of saturation. This condition will shorten the off time at frequencies ≥ 30 kHz, and is magnified at high temperatures. This condition does not occur with a Darlington configuration, since the output switch cannot saturate. If a non-Darlington configuration is used, the following output drive condition is recommended:

<sup>\*</sup> The 100  $\Omega$  resistor in the emitter of the driver device requires about 7.0 mA before the output switch conducts.

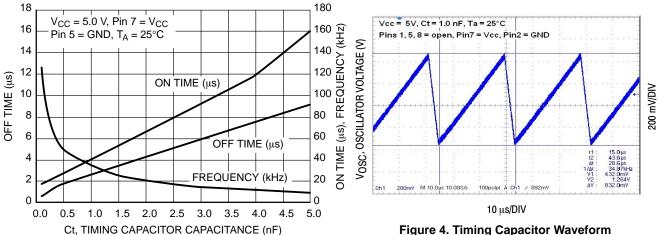


Figure 3. Oscillator Frequency

Figure 4. Timing Capacitor Waveform

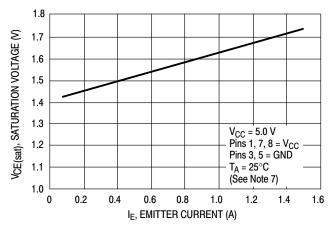
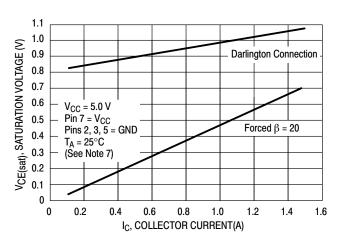


Figure 5. Emitter Follower Configuration Output **Saturation Voltage versus Emitter Current** 



**Figure 6. Common Emitter Configuration Output Switch Saturation Voltage versus Collector Current** 

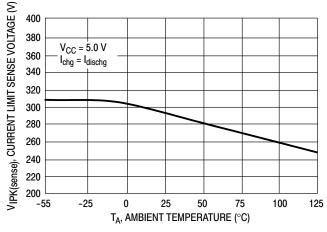


Figure 7. Current Limit Sense Voltage versus Temperature

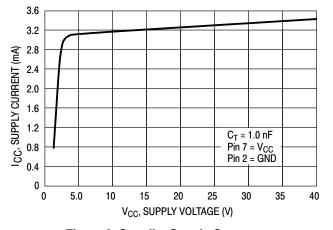
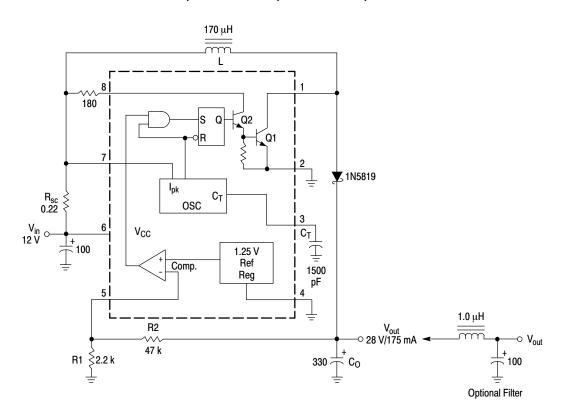


Figure 8. Standby Supply Current versus Supply Voltage

7. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.



Test	Conditions	Results
Line Regulation	$V_{in} = 8.0 \text{ V to } 16 \text{ V}, I_{O} = 175 \text{ mA}$	$30 \text{ mV} = \pm 0.05\%$
Load Regulation	V <sub>in</sub> = 12 V, I <sub>O</sub> = 75 mA to 175 mA	10 mV = ±0.017%
Output Ripple	V <sub>in</sub> = 12 V, I <sub>O</sub> = 175 mA	400 mVpp
Efficiency	V <sub>in</sub> = 12 V, I <sub>O</sub> = 175 mA	87.7%
Output Ripple With Optional Filter	V <sub>in</sub> = 12 V, I <sub>O</sub> = 175 mA	40 mVpp

Figure 9. Step-Up Converter

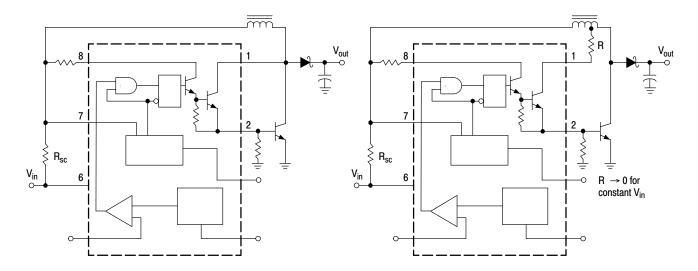


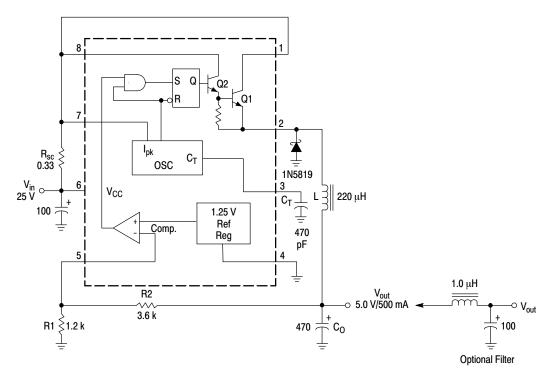
Figure 10. External Current Boost Connections for I<sub>C</sub> Peak Greater than 1.5 A

9a. External NPN Switch

9b. External NPN Saturated Switch

(See Note 8)

8. If the output switch is driven into hard saturation (non–Darlington configuration) at low switch currents (≤ 300 mA) and high driver currents (≥30 mA), it may take up to 2.0 μs to come out of saturation. This condition will shorten the off time at frequencies ≥ 30 kHz, and is magnified at high temperatures. This condition does not occur with a Darlington configuration, since the output switch cannot saturate. If a non–Darlington configuration is used, the following output drive condition is recommended.



Test	Conditions	Results
Line Regulation	V <sub>in</sub> = 15 V to 25 V, I <sub>O</sub> = 500 mA	12 mV = ±0.12%
Load Regulation	$V_{in} = 25 \text{ V}, I_{O} = 50 \text{ mA to } 500 \text{ mA}$	$3.0 \text{ mV} = \pm 0.03\%$
Output Ripple	V <sub>in</sub> = 25 V, I <sub>O</sub> = 500 mA	120 mVpp
Short Circuit Current	$V_{in}$ = 25 V, $R_L$ = 0.1 $\Omega$	1.1 A
Efficiency	V <sub>in</sub> = 25 V, I <sub>O</sub> = 500 mA	83.7%
Output Ripple With Optional Filter	V <sub>in</sub> = 25 V, I <sub>O</sub> = 500 mA	40 mVpp

Figure 11. Step-Down Converter

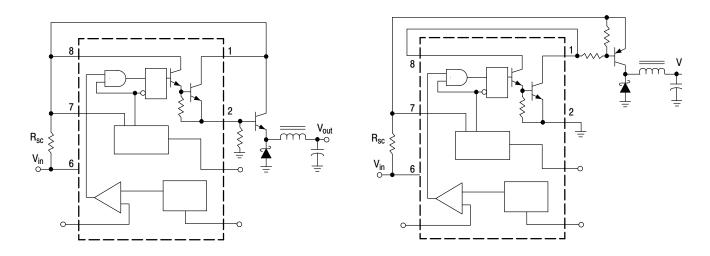
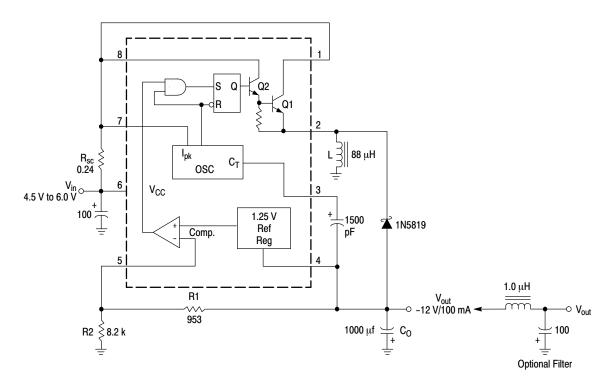


Figure 12. External Current Boost Connections for  $I_{\mbox{\scriptsize C}}$  Peak Greater than 1.5 A

11a. External NPN Switch

11b. External PNP Saturated Switch



Test	Conditions	Results
Line Regulation	V <sub>in</sub> = 4.5 V to 6.0 V, I <sub>O</sub> = 100 mA	$3.0 \text{ mV} = \pm 0.012\%$
Load Regulation	$V_{in} = 5.0 \text{ V}, I_O = 10 \text{ mA to } 100 \text{ mA}$	$0.022 \text{ V} = \pm 0.09\%$
Output Ripple	$V_{in} = 5.0 \text{ V}, I_{O} = 100 \text{ mA}$	500 mVpp
Short Circuit Current	$V_{in} = 5.0 \text{ V}, R_L = 0.1 \Omega$	910 mA
Efficiency	V <sub>in</sub> = 5.0 V, I <sub>O</sub> = 100 mA	62.2%
Output Ripple With Optional Filter	V <sub>in</sub> = 5.0 V, I <sub>O</sub> = 100 mA	70 mVpp

Figure 13. Voltage Inverting Converter

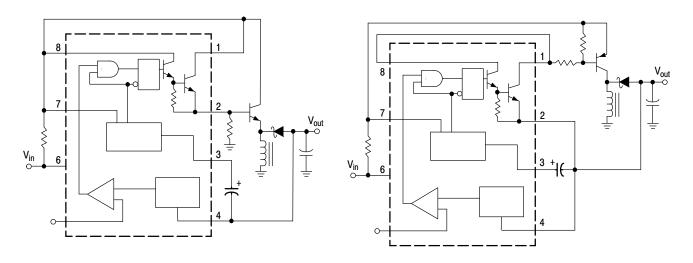
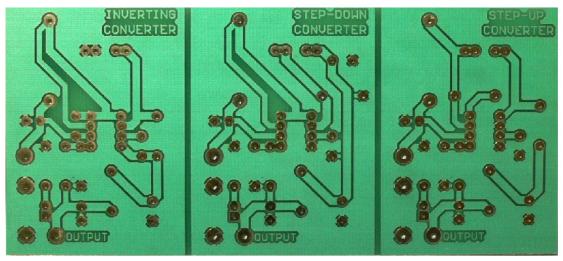


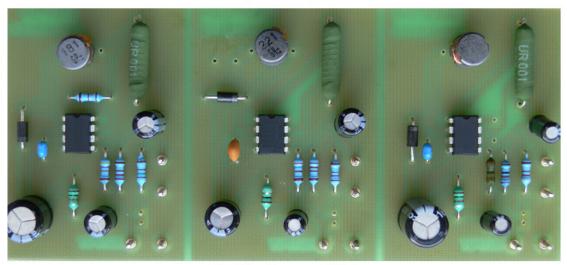
Figure 14. External Current Boost Connections for I<sub>C</sub> Peak Greater than 1.5 A

13a. External NPN Switch

13b. External PNP Saturated Switch



(Bottom Side)



(Top View, Component Side)

Figure 15. Printed Circuit Board and Component Layout

(Circuits of Figures 9, 11, 13)

# **INDUCTOR DATA**

Converter	Inductance (μH)	Turns/Wire
Step-Up	170	38 Turns of #22 AWG
Step-Down	220	48 Turns of #22 AWG
Voltage-Inverting	88	28 Turns of #22 AWG

All inductors are wound on Magnetics Inc. 55117 toroidal core.

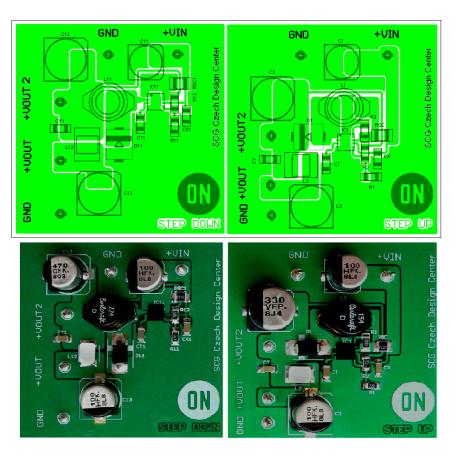


Figure 16. Printed Circuit Board for DFN Device

Calculation	Step-Up	Step-Down	Voltage-Inverting
t <sub>on</sub> /t <sub>off</sub>	$\frac{V_{\text{out}} + V_{\text{F}} - V_{\text{in(min)}}}{V_{\text{in(min)}} - V_{\text{sat}}}$	$\frac{V_{out} + V_{F}}{V_{in(min)} - V_{sat} - V_{out}}$	$\frac{ V_{out}  + V_F}{V_{in} - V_{sat}}$
$(t_{on} + t_{off})$	<u>1</u>	$\frac{1}{f}$	$\frac{1}{f}$
t <sub>off</sub>	$\frac{t_{\text{on}} + t_{\text{off}}}{\frac{t_{\text{on}}}{t_{\text{off}}} + 1}$	$\frac{t_{\text{on}} + t_{\text{off}}}{\frac{t_{\text{on}}}{t_{\text{off}}} + 1}$	$\frac{t_{\text{on}} + t_{\text{off}}}{\frac{t_{\text{on}}}{t_{\text{off}}}} + 1$
t <sub>on</sub>	$(t_{on} + t_{off}) - t_{off}$	$(t_{on} + t_{off}) - t_{off}$	$(t_{on} + t_{off}) - t_{off}$
C <sub>T</sub>	4.0 x 10 <sup>-5</sup> t <sub>on</sub>	4.0 x 10 <sup>-5</sup> t <sub>on</sub>	$4.0 \times 10^{-5} t_{on}$
I <sub>pk(switch)</sub>	$2l_{out(max)} \left( \frac{t_{on}}{t_{off}} + 1 \right)$	<sup>2I</sup> out(max)	$2l_{out(max)} \left(\frac{t_{on}}{t_{off}} + 1\right)$
R <sub>sc</sub>	0.3/I <sub>pk(switch)</sub>	0.3/I <sub>pk(switch)</sub>	0.3/I <sub>pk(switch)</sub>
L <sub>(min)</sub>	$\left(\frac{(V_{in(min)} - V_{sat})}{I_{pk(switch)}}\right)^{t} on(max)$	$\left(\frac{(V_{in(min)} \ - \ V_{sat} \ - \ V_{out})}{I_{pk(switch)}}\right) t_{on(max)}$	$\left(\frac{(V_{\text{in(min)}} - V_{\text{sat}})}{I_{\text{pk(switch)}}}\right)^{t_{\text{on(max)}}}$
Co	9	$\frac{I_{pk(switch)}^{(t_{on} + t_{off})}}{8V_{ripple(pp)}}$	$9 \frac{I_{out}t_{on}}{V_{ripple(pp)}}$

 $V_{sat}$  = Saturation voltage of the output switch.

## The following power supply characteristics must be chosen:

V<sub>in</sub> – Nominal input voltage.

 $V_{out}$  - Desired output voltage,  $|V_{out}| = 1.25 \left(1 + \frac{R2}{R1}\right)$ 

I<sub>out</sub> – Desired output current.

 $f_{min}$  – Minimum desired output switching frequency at the selected values of  $V_{in}$  and  $I_{O}$ .

V<sub>ripple(pp)</sub> – Desired peak–to–peak output ripple voltage. In practice, the calculated capacitor value will need to be increased due to its equivalent series resistance and board layout. The ripple voltage should be kept to a low value since it will directly affect the line and load regulation.

**NOTE:** For further information refer to Application Note AN920A/D and AN954/D.

Figure 17. Design Formula Table

V<sub>F</sub> = Forward voltage drop of the output rectifier.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC33063ADG	SOIC-8 (Pb-Free)	98 Units / Rail
MC33063ADR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
SC33063ADR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
MC33063AP1G	PDIP-8 (Pb-Free)	50 Units / Rail
MC33063AVDG	SOIC-8 (Pb-Free)	98 Units / Rail
MC33063AVDR2G	SOIC-8 (Pb-Free)	
NCV33063AVDR2G*	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
MC33063AVPG	PDIP-8 (Pb-Free)	50 Units / Rail
MC34063ADG	SOIC-8 (Pb-Free)	98 Units / Rail
MC34063ADR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
MC34063AP1G	PDIP-8 (Pb-Free)	50 Units / Rail

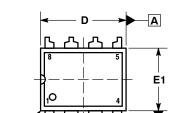
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

<sup>\*</sup>NCV33063A:  $T_{low} = -40$ °C,  $T_{high} = +125$ °C. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.



PDIP-8 CASE 626-05 ISSUE P

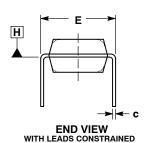
**DATE 22 APR 2015** 



**TOP VIEW** 

b2

В



NOTE 5

e/2 NOTE 3 SEATING PLANE C D1 eВ 8X b **END VIEW** |⊕|0.010 M| C| A M| B M NOTE 6 SIDE VIEW

STYLE 1: PIN 1. AC IN 2. DC + IN 3. DC - IN 4. AC IN 5. GROUND 6. OUTPUT 7. AUXILIARY 8. V<sub>CC</sub>

#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: INCHES.
  DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACK-
- AGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
  DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
- DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR
- 6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE
- LEADS UNCONSTRAINED.

  DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
- PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α		0.210		5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060	TYP	1.52	TYP
С	0.008	0.014	0.20	0.36
D	0.355	0.400	9.02	10.16
D1	0.005		0.13	
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100	BSC	2.54	BSC
eВ		0.430		10.92
L	0.115	0.150	2.92	3.81
М		10°		10°

# **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code = Assembly Location

WL = Wafer Lot YY = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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#### SOIC-8 NB CASE 751-07 **ISSUE AK**

**DATE 16 FEB 2011** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27	7 BSC	0.050 BSC	
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

# **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location = Wafer Lot = Year = Work Week W

= Pb-Free Package

XXXXXX XXXXXX AYWW AYWW Ŧ  $\mathbb{H}$ Discrete **Discrete** (Pb-Free)

XXXXXX = Specific Device Code = Assembly Location Α = Year ww = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

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## SOIC-8 NB CASE 751-07 ISSUE AK

# **DATE 16 FEB 2011**

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE. #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16:  PIN 1. EMITTER, DIE #1  2. BASE, DIE #1  3. EMITTER, DIE #2  4. BASE, DIE #2  5. COLLECTOR, DIE #2  7. COLLECTOR, DIE #2  8. COLLECTOR, DIE #1  8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW TO GND 2. DASIC OFF 3. DASIC SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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